## **TOSHIBA**

# MICROWAVE SEMICONDUCTOR TECHNICAL DATA

#### MICROWAVE POWER GaAs FET

#### TIM3742-16SL

#### **FEATURES:**

- LOW INTERMODULATION DISTORTION IM<sub>3</sub> = -45 dBc at Po = 31.5 dBm, Single Carrier Level
- HIGH POWER

 $P_{1dB} = 42.5 \text{ dBm at } 3.7 \text{GHz to } 4.2 \text{ GHz}$ 

HIGH GAIN

 $G_{1dB} = 9.5$  dB at 3.7 GHz to 4.2 GHz

- **■** BROAD BAND INTERNALLY MATCHED
- HERMETICALLY SEALED PACKAGE

### RF PERFORMANCE SPECIFICATIONS (Ta = 25°C)

CHARACTERISTICS	SYMBOL	CONDITION	UNIT	MIN.	TYP.	MAX.
Output Power at 1 dB Compression Point	P <sub>1dB</sub>	V <sub>DS</sub> = 10 V f = 3.7~4.2GHz	dBm	41.5	42.5	
Power Gain at 1 dB Compression Point	G <sub>1dB</sub>		dB	8.5	9.5	
Drain Current	I <sub>DS</sub>		Α	_	4.4	5.0
Gain Flatness	ΔG		dB	_	-	± 0.8
Power Added Efficiency	7add		%	_	36	_
3rd Order Intermodulation Distortion	IM <sub>3</sub>	Note 1	dBc	-42	<b>– 45</b>	_
Channel-Temperature Rise	ΔTch	$V_{DS} \times I_{DS} \times R_{th} (c-c)$	°C	_	_	80

## **ELECTRICAL CHARACTERISTICS (Ta = 25°C)**

CHARACTERISTICS	SYMBOL	CONDITION	UNIT	MIN.	TYP.	MAX.
Transconductance	gm	$V_{DS} = 3 V$ $I_{DS} = 6.0 A$	mS	_	3600	_
Pinch-off Voltage	V <sub>GSoff</sub>	$V_{DS} = 3 V$ $I_{DS} = 60 \text{ mA}$	V	-1	-2.5	-4.0
Saturated Drain Current	I <sub>DSS</sub>	$V_{DS} = 3 V$ $V_{GS} = 0 V$	А	_	10.5	14.0
Gate-Source Breakdown Voltage	V <sub>GSO</sub>	I <sub>GS</sub> =- 200 μA	V	-5	_	_
Thermal Resistance	R <sub>th (c-c)</sub>	Channel to Case	°C/W	-	1.5	2.0

Note 1: 2 tone Test Pout = 31.5 dBm Single Carrier Level.

<sup>★</sup> The information contained herein may be changed without prior notice. It is therefore advisable to contact TOSHIBA before proceeding with the design of equipment incorporating this product.

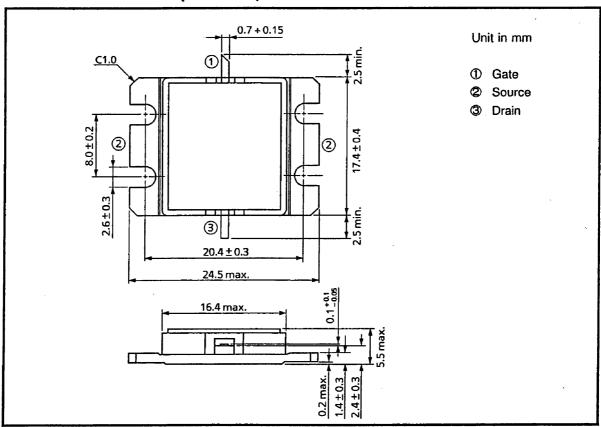


<sup>★</sup> The information contained herein is presented only as a guide for the applications of our products. No responsibility is assumed by TOSHIBA for any infringements of patents or other rights of the third parties which may result from its use. No license is granted by implication or otherwise under any patent or patent rights of TOSHIBA or others.

## ABSOLUTE MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTICS	SYMBOL	UNIT	RATING
Drain-Source Voltage	V <sub>DS</sub>	V	15
Gate-Source Voltage	V <sub>GS</sub>	V	5
Drain Current	IDS	Α	14
Total Power Dissipation (T <sub>C</sub> = 25°C)	P <sub>T</sub>	W	75
Channel Temperature	T <sub>ch</sub>	°C	175
Storage Temperature	T <sub>stg</sub>	°C	<b> 65∼175</b>

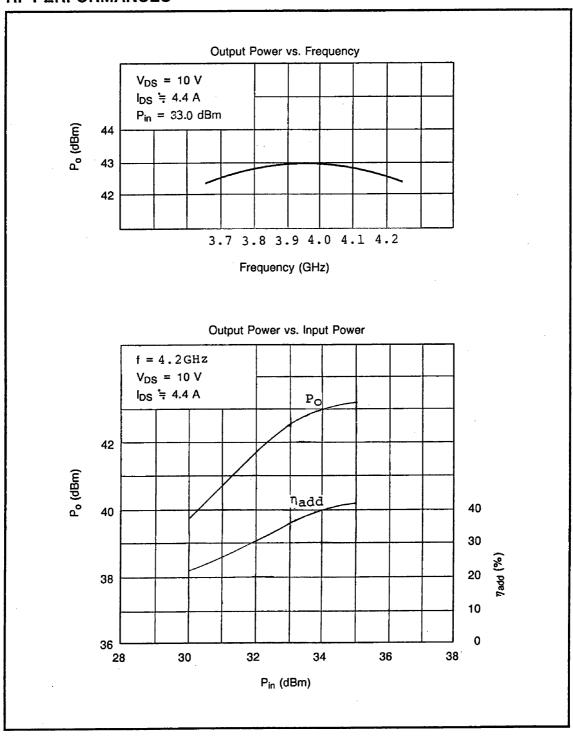
## PACKAGE OUTLINE (2-16G1B)



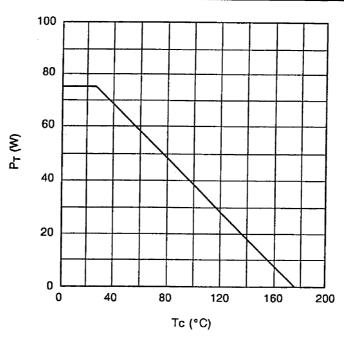
#### HANDLING PRECAUTIONS FOR PACKAGED TYPE

Soldering iron should be grounded and the operating time should not exceed 10 seconds at 260°C.

#### **RF PERFORMANCES**



## **POWER DISSIPATION VS. CASE TEMPERATURE**



### IM<sub>3</sub> VS. OUTPUT POWER CHARACTERISTICS

